

SEMICONDUCTOR®

# BD676A/678A/680A/682

# Medium Power Linear and Switching Applications

Medium Power Darlington TR

Complement to BD675A, BD677A, BD679A and BD681 respectively

## **PNP Epitaxial Silicon Transistor**



BD676A/678A/680A/682

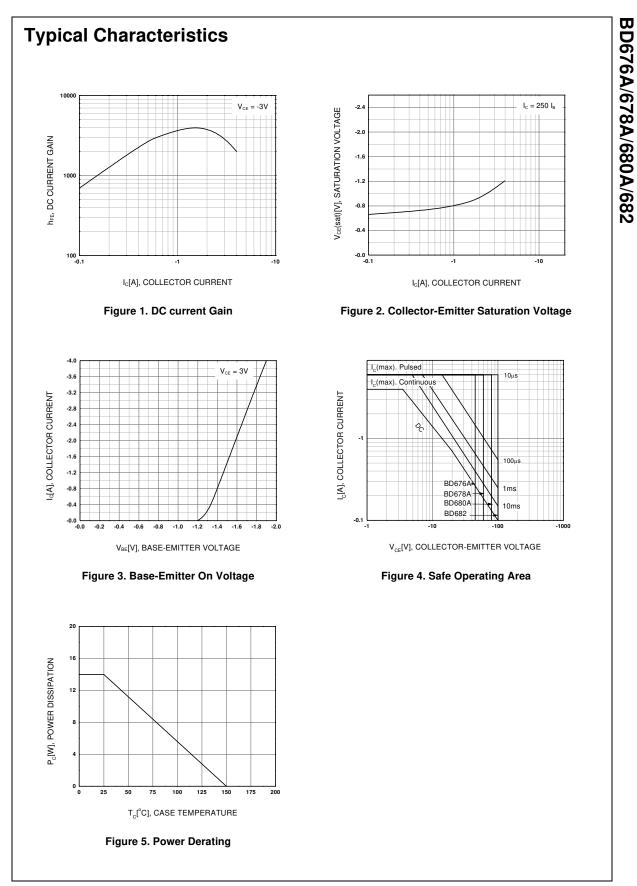
## Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CBO</sub>	Collector-Base Voltage : BD676A	- 45	V	
	: BD678A	- 60	V	
	: BD680A	- 80	V	
	: BD682	- 100	V	
V <sub>CEO</sub>	Collector-Emitter Voltage : BD676A	- 45	V	
	: BD678A	- 60	V	
	: BD680A	- 80	V	
	: BD682	- 100	V	
V <sub>EBO</sub>	Emitter-Base Voltage	- 5	V	
lc	Collector Current (DC)	- 4	А	
CP	*Collector Current (Pulse)	- 6	А	
в	Base Current	- 100	mA	
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	14	W	
R <sub>θja</sub>	Thermal Resistance (Junction to Ambient)	88	°C/W	
TJ	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C	

### Electrical Characteristics $T_{C}=25^{\circ}C$ unless otherwise noted

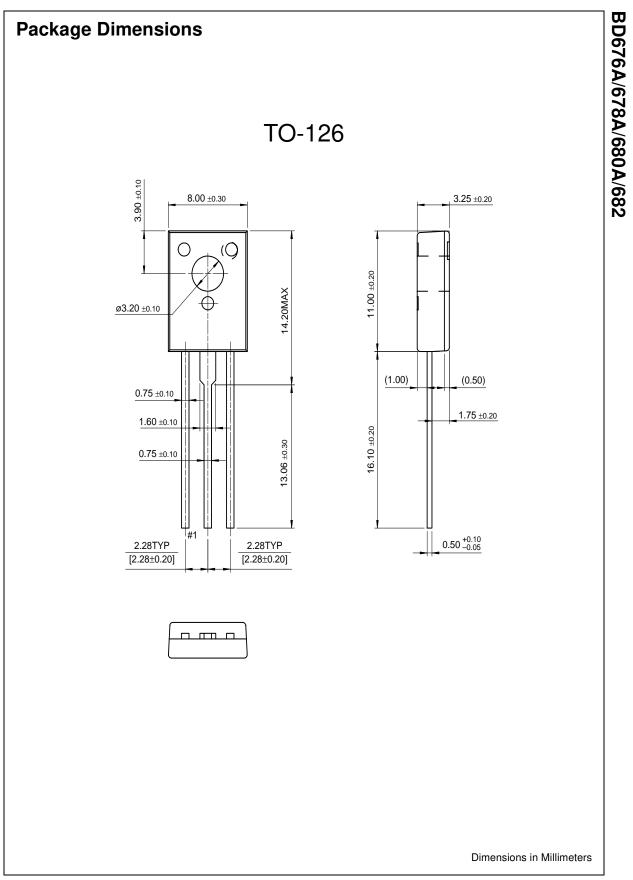
Symbol	Paran	neter	Test Condition	Min.	Тур.	Max.	Unit
V <sub>CEO</sub> (sus)	Collector-Emitter Sustaini	ng Voltage					
		: BD676A	I <sub>C</sub> = - 50mA, I <sub>B</sub> = 0	- 45			
		: BD678A		- 60			
		: BD680A		- 80			
		: BD682		- 100			
I <sub>CBO</sub>	Collector-Base Voltage	: BD676A	V <sub>CB</sub> = - 45V, I <sub>E</sub> = 0			- 200	μA
		: BD678A	$V_{CB} = -60V, I_E = 0$			- 200	μA
		: BD680A	$V_{CB} = -80V, I_E = 0$			- 200	μA
		: BD682	$V_{CB} = -100V, V_{BE} = 0$			- 200	μA
I <sub>CEO</sub>	Collector Cut-off Current	: BD676A	$V_{CE} = -45V, V_{BE} = 0$			- 500	μA
		: BD678A	$V_{CE} = -60V, V_{BE} = 0$			- 500	μA
		: BD680A	$V_{CE} = -80V, V_{BE} = 0$			- 500	μA
		: BD682	$V_{CE} = -100V, V_{BE} = 0$			- 500	μA
I <sub>EBO</sub>	Emitter Cut-off Current		$V_{EB} = -5V, I_{C} = 0$			- 2	m/
h <sub>FE</sub>	* DC Current Gain	: BD676A/678A/680A	V <sub>CE</sub> = - 3V, I <sub>C</sub> = - 2A	750			
		: BD682	V <sub>CE</sub> = - 3V, I <sub>C</sub> = - 1.5A	750			
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage						
		: BD676A/678A/680A	I <sub>C</sub> = - 2A, I <sub>B</sub> = - 40mA			- 2.8	V
		: BD682	I <sub>C</sub> = - 1.5A, I <sub>B</sub> = - 30mA			- 2.5	V
V <sub>BE</sub> (on)	* Base-Emitter On Voltage	e : BD676A/678A/680A	V <sub>CE</sub> = - 3V, I <sub>C</sub> = - 2A			- 2.5	V
		: BD682	$V_{CF} = -3V, I_{C} = -1.5A$			- 2.5	V

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